



Silicon Wafer Japan TC Chapter

Japan Standards Winter 2022 Meetings

Friday, January 28, 2022

<10:00 –12:00 JST> via Virtual Meeting

AGENDA

| | Time |
|---|--------------|
| 1 Welcome/Call to Order | 10:00 |
| 1.1 Introductions | |
| 1.2 Required Elements (Membership Requirements, Antitrust and Intellectual Property Reminders, and Effective Meeting Guidelines) | |
| 1.3 Agenda Review | |
| 2 Review of Previous Meeting Minutes | |
| 3 Ballot Review | |
| 3.1 Cycle 7-2021 submitted by the NA TC Chapter (the GCS authorized to transfer responsibilities for Letter Ballot review from the NA TC Chapter to the Japan Chapter of Silicon Wafer Committee for these documents) | |
| 3.1.1 Doc6853, Reapproval of SEMI MF978-1106 (Reapproved 0317) Test Method for Characterizing Semiconductor Deep Levels by Transient Capacitance Techniques | |
| 3.1.2 Doc6854, Reapproval of SEMI MF928-0317, Test Method for Edge Contour of Circular Semiconductor Wafers and Rigid Disk Substrates | |
| 3.1.3 Doc6855, Reapproval of SEMI MF728-1106 (Reapproved 0317) Practice for Preparing an Optical Microscope for Dimensional Measurements | |
| 3.1.4 Doc6856, Reapproval of SEMI MF673-0317, Test Method for Measuring Resistivity of Semiconductor Wafers or Sheet Resistance of Semiconductor Films with a Noncontact Eddy-Current Gauge | |
| 3.1.5 Doc6857, Reapproval of SEMI MF28-0317, Test Method for Minority Carrier Lifetime in Bulk Germanium and Silicon by Measurement of Photoconductivity Deca | |
| 4 Subcommittee & Task Force Reports | |
| 4.1 International Advanced Wafer Geometry TF | |
| 4.2 Japan Test Method TF | |
| 4.3 International Advanced Surface Inspection TF | |
| 4.4 International Polished Wafers TF | |
| 4.5 International Epitaxial Wafers TF | |
| 4.6 International Annealed Wafers TF | |
| 4.7 International SOI Wafers TF | |

4.8 International Terminology TF

5 Liaison Report

5.1 Europe TC Chapter

5.2 North America TC Chapter

5.3 GCS Report

6 Staff Report

7 Old Business

7.1 Project Period Review

7.1.1 #6570 SNARF for: New Standard: Guide for Measuring Bulk Micro Defect Density and Denuded Zone Width in Annealed Silicon Wafers by a Laser-Scatter Tomography Technique

7.2 5 Year Review Check

7.2.1 SEMI M51-1012: Test Method for Characterizing Silicon Wafer by Gate Oxide Integrity

7.2.2 SEMI M60-1014: Test Method for Time Dependent Dielectric Breakdown Characteristics of SiO₂ Films for Si Wafer Evaluation

8 New Business

None

9 Action Item Review

9.1 Open Action Items

9.2 New Action Items

10 Next Meeting and Adjournment

12:00

10.1 The next meeting is scheduled for <date> at <event/location>.